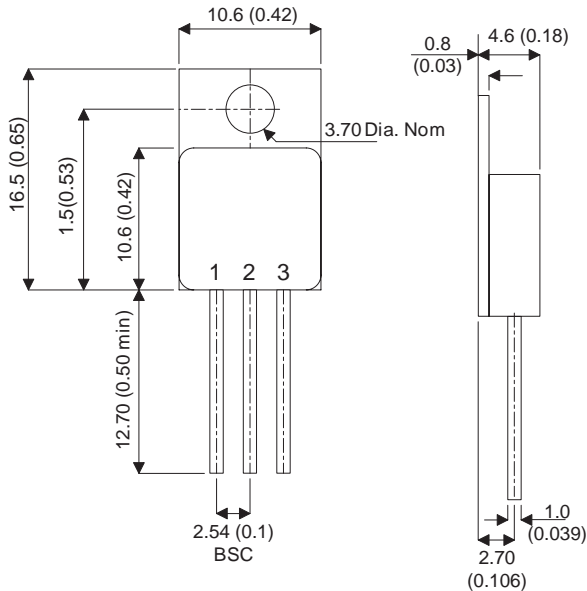


Dimensions in mm (inches).



N-Channel MOSFET in a Hermetically sealed TO257AB Metal Package.

$$V_{DSS} = 200V$$

$$I_D = 9A$$

$$R_{DS(ON)} = 0.4\Omega$$

All Semelab hermetically sealed products can be processed in accordance with the requirements of BS, CECC and JAN, JANTX, JANTXV and JANS specifications.

TO257AB (TO220M)

PINOUTS

1 – Gate 2 – Drain Case – Source

| | Parameter | Min. | Typ. | Max. | Units |
|---------------|---|------|------|------|----------|
| V_{DSS} | Drain – Source Breakdown Voltage | | | 200 | V |
| I_D | Continuous Drain Current | | | 9 | A |
| P_D | Power Dissipation | | | 75 | W |
| $R_{DS(ON)}$ | Static Drain – Source On–State Resistance | | | 0.4 | Ω |
| C_{ISS} | Input Capacitance | | 600 | | pF |
| Q_g | Total Gate Charge | | | 39 | nC |
| $t_{td(on)}$ | Turn–On Delay Time | | | 35 | ns |
| t_{tr} | Rise Time | | | 80 | ns |
| $t_{td(off)}$ | Turn–Off Delay Time | | | 60 | ns |
| t_f | Fall Time | | | 40 | ns |

This is a shortform datasheet. For a full datasheet please contact sales@semelab.co.uk.

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use.